- **Member of the Texas Instruments Widebus ™ Family**
- **Free-Running Read and Write Clocks Can Be Asynchronous or Coincident**
- **Read and Write Operations Synchronized to Independent System Clocks**
- **Input-Ready Flag Synchronized to Write Clock**
- **Output-Ready Flag Synchronized to Read Clock**
- **512 Words by 18 Bits**
- **Low-Power Advanced CMOS Technology**
- **Half-Full Flag and Programmable Almost-Full/Almost-Empty Flag**
- **Bidirectional Configuration and Width Expansion Without Additional Logic**
- **Fast Access Times of 12 ns With a 50-pF Load and All Data Outputs Switching Simultaneously**
- **Data Rates From 0 to 67 MHz**
- **Pin Compatible With SN74ACT7805 and SN74ACT7813**
- **Available in Shrink Small-Outline 300-mil (DL) Package Using 25-mil Center-to-Center Spacing**

DL PACKAGE
(TOP VIEW)

$\overline{\text{RESET}}$	1	56	$\overline{\text{OE1}}$
D17	2	55	Q17
D16	3	54	Q16
D15	4	53	Q15
D14	5	52	GND
D13	6	51	Q14
D12	7	50	V_{CC}
D11	8	49	Q13
D10	9	48	Q12
V_{CC}	10	47	Q11
D9	11	46	Q10
D8	12	45	Q9
GND	13	44	GND
D7	14	43	Q8
D6	15	42	Q7
D5	16	41	Q6
D4	17	40	Q5
D3	18	39	V_{CC}
D2	19	38	Q4
D1	20	37	Q3
D0	21	36	Q2
HF	22	35	GND
$\overline{\text{PEN}}$	23	34	Q1
AF/AE	24	33	Q0
WRTCLK	25	32	RDCLK
$\overline{\text{WRTEN2}}$	26	31	$\overline{\text{RDEN}}$
WRTEN1	27	30	$\overline{\text{OE2}}$
IR	28	29	OR

description

The SN74ACT7803 is a 512-word × 18-bit FIFO suited for buffering asynchronous data paths at 67-MHz clock rates and 12-ns access times. Its 56-pin shrink small-outline package (DL) offers greatly reduced board space over DIP, PLCC, and conventional SOIC packages. Two devices can be configured for bidirectional data buffering without additional logic. Multiple distributed V_{CC} and GND pins along with TI's patented output-edge-control (OEC™) circuit dampen simultaneous switching noise.

The write clock (WRTCLK) and read clock (RDCLK) should be free running and can be asynchronous or coincident. Data is written to memory on the rising edge of WRTCLK when WRTEN1 is high, $\overline{\text{WRTEN2}}$ is low, and IR is high. Data is read from memory on the rising edge of RDCLK when $\overline{\text{RDEN}}$, $\overline{\text{OE1}}$, and $\overline{\text{OE2}}$ are low and OR is high. The first word written to memory is clocked through to the output buffer regardless of the $\overline{\text{RDEN}}$, $\overline{\text{OE1}}$, and $\overline{\text{OE2}}$ levels. The OR flag indicates that valid data is present on the output buffer.

The FIFO can be reset asynchronously to WRTCLK and RDCLK. $\overline{\text{RESET}}$ must be asserted while at least four WRTCLK and four RDCLK rising edges occur to clear the synchronizing registers. Resetting the FIFO initializes the IR, OR, and HF flags low and the AF/AE flag high. The FIFO must be reset upon power up.

The SN74ACT7803 is characterized for operation from 0°C to 70°C.

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logic symbol†
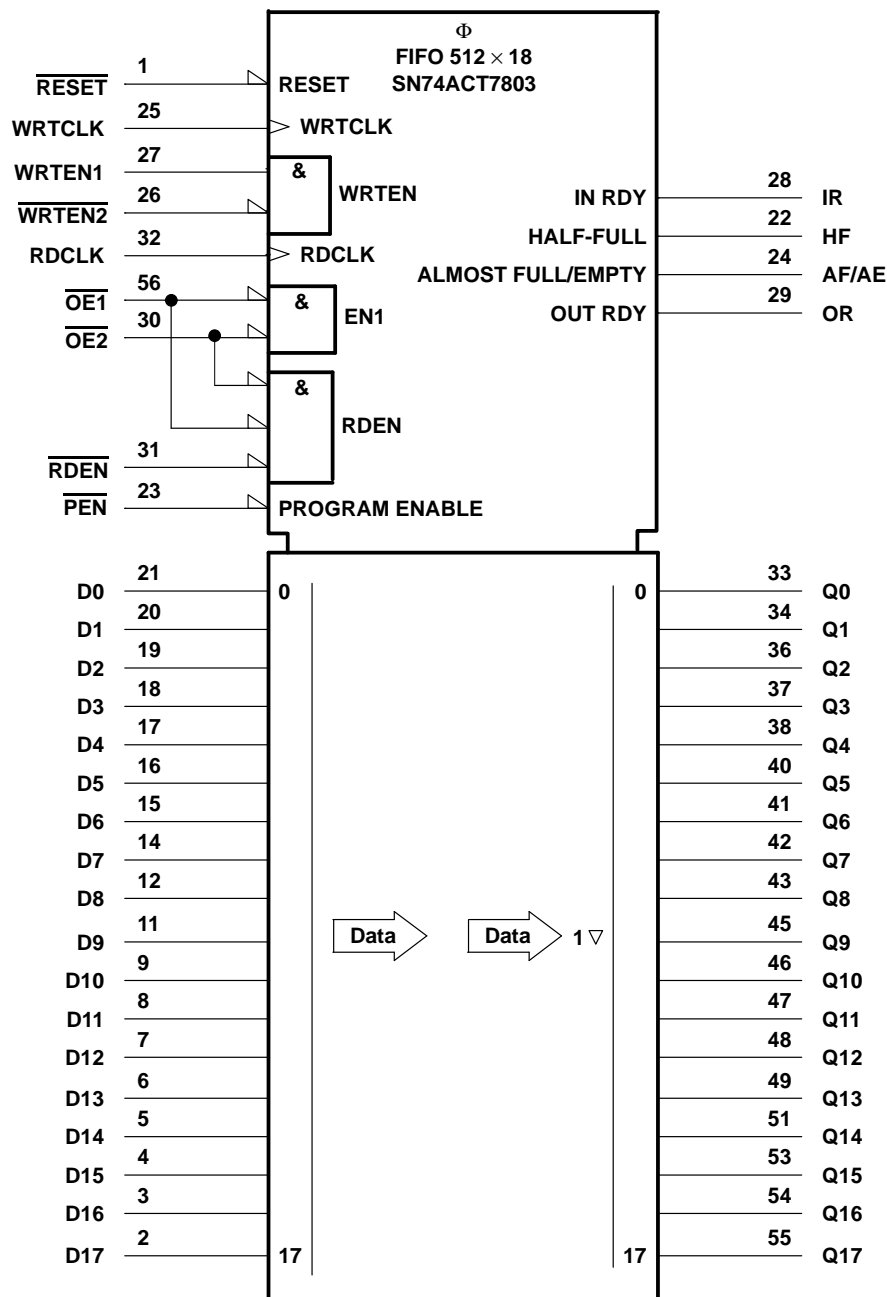
† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

functional block diagram
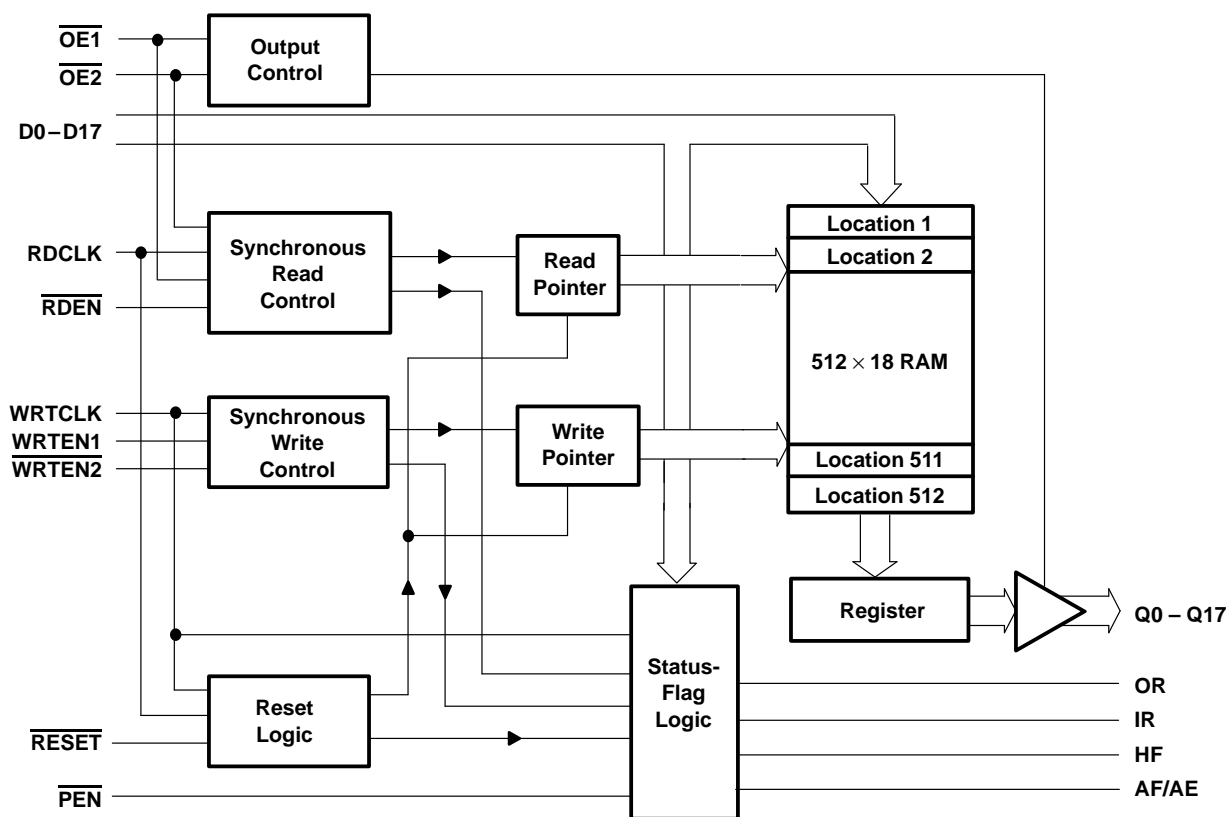
Terminal Functions

| TERMINAL		I/O	DESCRIPTION
NAME	NO.		
AF/AE	24	O	Almost-full/almost-empty flag. Depth-offset values can be programmed for AF/AE, or the default value of 64 can be used for both the almost-empty offset (X) and the almost-full offset (Y). AF/AE is high when memory contains X or less words or (512 – Y) or more words. AF/AE is high after reset.
D0–D17	2–9, 11–12, 14–21	I	The 18-bit data input port
HF	22	O	Half-full flag. HF is high when the FIFO memory contains 256 or more words. HF is low after reset.
IR	28	O	Input-ready flag. IR is synchronized to the low-to-high transition of WRTCLK. When IR is low, the FIFO is full and writes are disabled. IR is low during reset and goes high on the second low-to-high transition of WRTCLK after reset.
$\overline{OE1}$, $\overline{OE2}$	56, 30	I	Output enables. When $\overline{OE1}$, $\overline{OE2}$, and $\overline{RDEN}$ are low and OR is high, data is read from the FIFO on a low-to-high transition of RDCLK. When either $\overline{OE1}$ or $\overline{OE2}$ is high, reads are disabled and the data outputs are in the high-impedance state.
OR	29	O	Output-ready flag. OR is synchronized to the low-to-high transition of RDCLK. When OR is low, the FIFO is empty and reads are disabled. Ready data is present on Q0–Q17 when OR is high. OR is low during reset and goes high on the third low-to-high transition of RDCLK after the first word is loaded to empty memory.
$\overline{PEN}$	23	I	Program enable. After reset and before the first word is written to the FIFO, the binary value on D0–D7 is latched as an AF/AE offset value when $\overline{PEN}$ is low and WRTCLK is high.
Q0–Q17	33–34, 36–38, 40–43, 45–49, 51, 53–55	O	The 18-bit data output port. After the first valid write to empty memory, the first word is output on Q0–Q17 on the third rising edge of RDCLK. OR is also asserted high at this time to indicate ready data. When OR is low, the last word read from the FIFO is present on Q0–Q17.
RDCLK	32	I	Read clock. RDCLK is a continuous clock and can be asynchronous or coincident to WRTCLK. A low-to-high transition of RDCLK reads data from memory when $\overline{OE1}$, $\overline{OE2}$, and $\overline{RDEN}$ are low and OR is high. OR is synchronous to the low-to-high transition of RDCLK.
$\overline{RDEN}$	31	I	Read enable. When $\overline{RDEN}$, $\overline{OE1}$, and $\overline{OE2}$ are low and OR is high, data is read from the FIFO on the low-to-high transition of RDCLK.
$\overline{RESET}$	1	I	Reset. To reset the FIFO, four low-to-high transitions of RDCLK and four low-to-high transitions of WRTCLK must occur while $\overline{RESET}$ is low. This sets HF, IR, and OR low and AF/AE high.
WRTCLK	25	I	Write clock. WRTCLK is a continuous clock and can be asynchronous or coincident to RDCLK. A low-to-high transition of WRTCLK writes data to memory when $\overline{WRTEN2}$ is low, WRTEN1 is high, and IR is high. IR is synchronous to the low-to-high transition of WRTCLK.
WRTEN1, $\overline{WRTEN2}$	27, 26	I	Write enables. When WRTEN1 is high, $\overline{WRTEN2}$ is low, and IR is high, data is written to the FIFO on a low-to-high transition of WRTCLK.
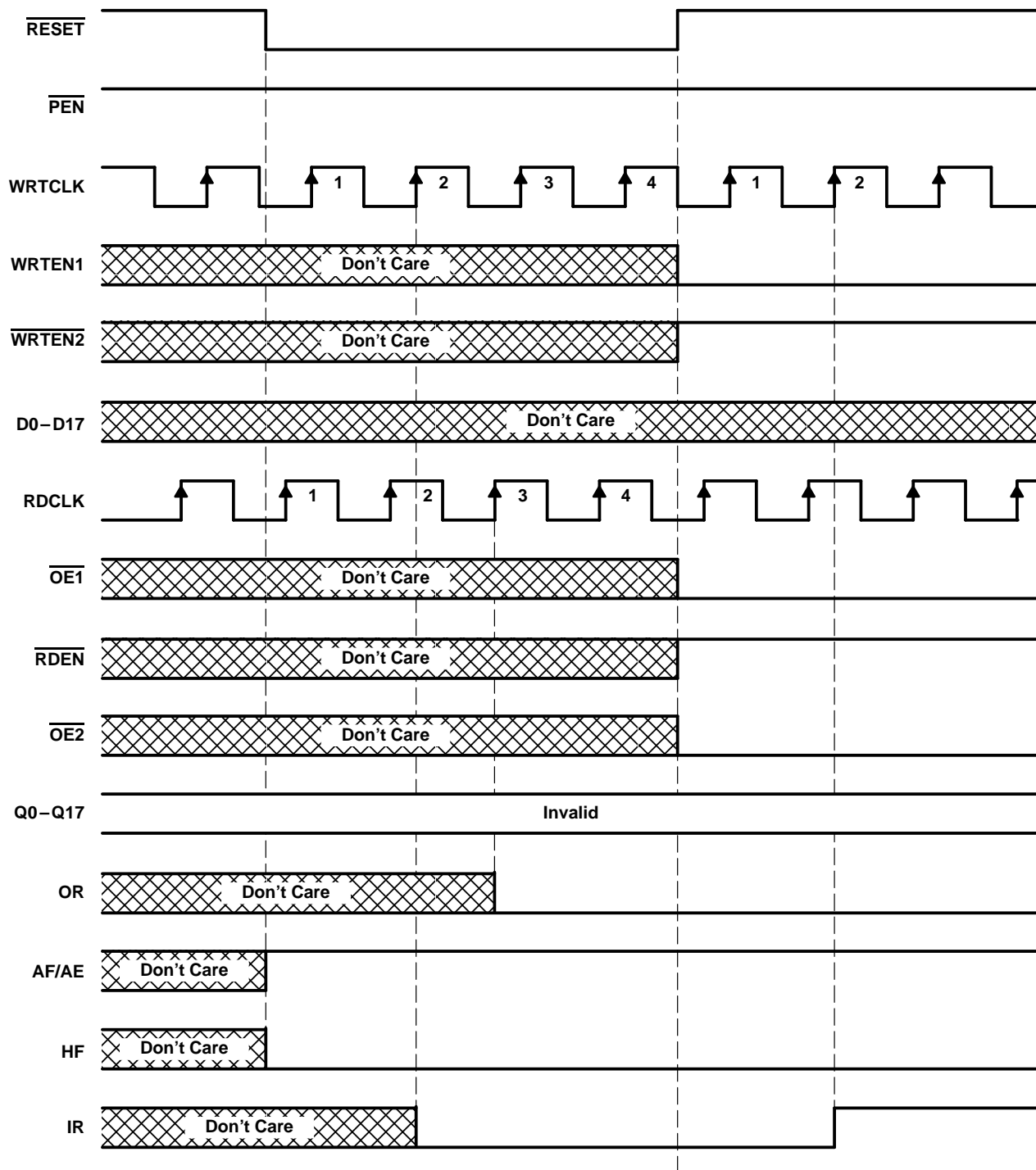
**Define the AF/AE Flag Using the
Default Value of X = Y = 64**

Figure 1. Reset Cycle
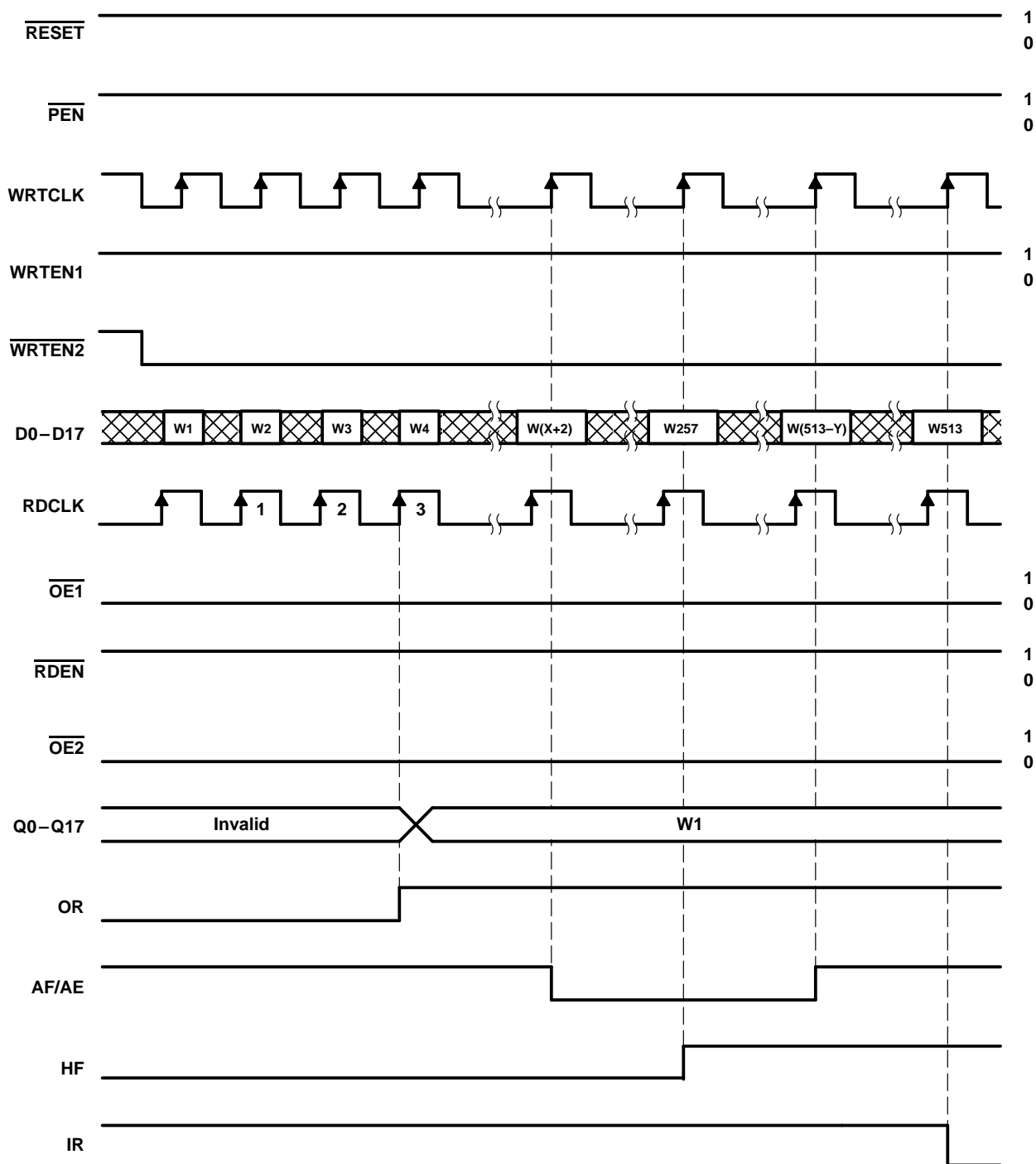
Figure 2. Write Cycle

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Figure 3. Read Cycle

offset values for AF/AE

The almost-full/almost-empty flag has two programmable limits: the almost-empty offset value (X) and the almost-full offset value (Y). They can be programmed after the FIFO is reset and before the first word is written to memory. If the offsets are not programmed, the default values of X = Y = 64 are used. The AF/AE flag is high when the FIFO contains X or less words or (512 – Y) or more words.

Program enable ($\overline{\text{PEN}}$) should be held high throughout the reset cycle. $\overline{\text{PEN}}$ can be brought low only when IR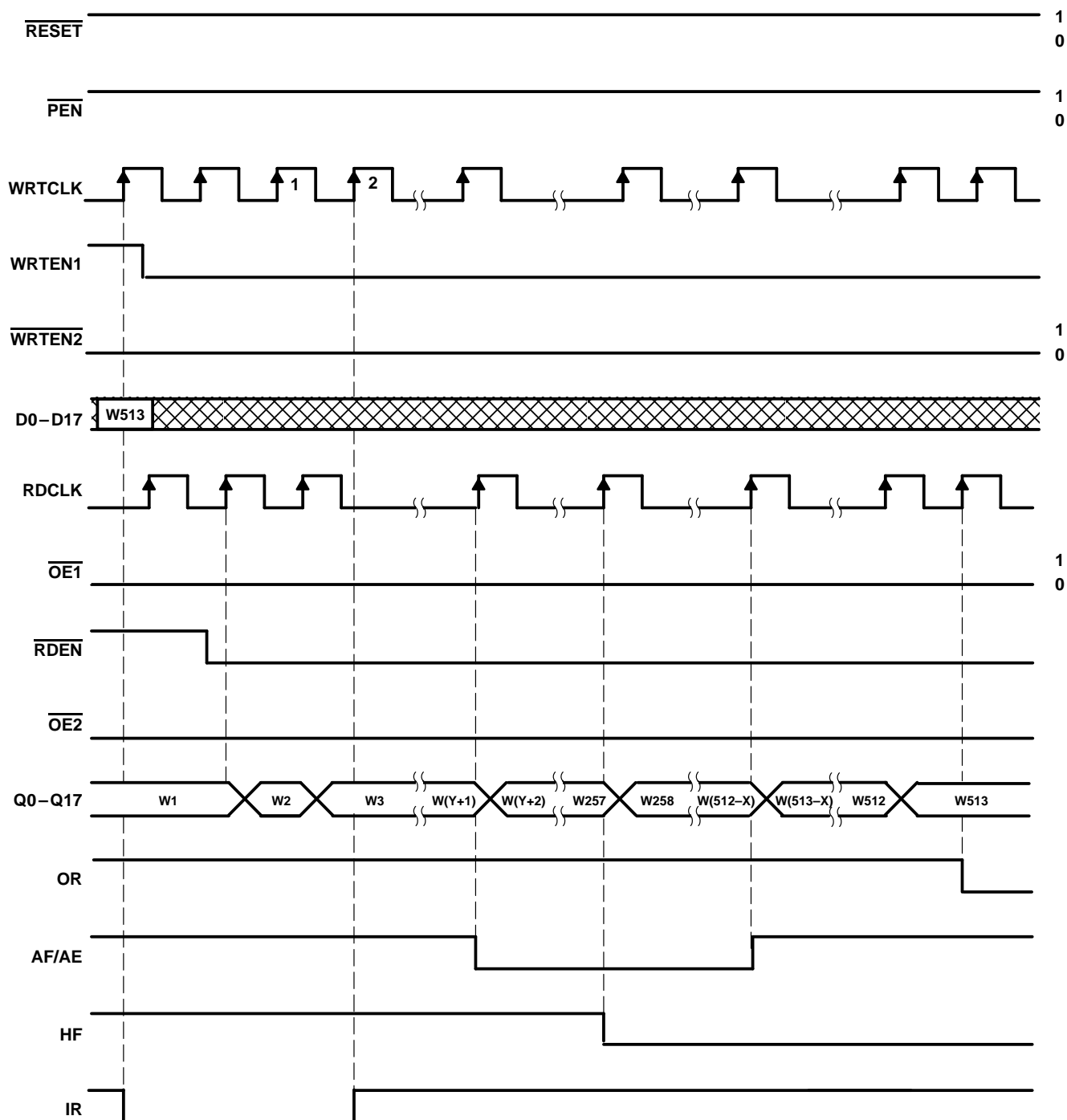 is high and WRTCLK is low. On the following low-to-high transition of WRTCLK, the binary value on D0–D7 is stored as the almost-empty offset value (X) and the almost-full offset value (Y). Holding $\overline{\text{PEN}}$ low for another low-to-high transition of WRTCLK reprograms Y to the binary value on D0–D7 at the time of the second WRTCLK low-to-high transition. When the offsets are being programmed, writes to the FIFO memory are disabled regardless of the state of the write enables (WRTEN1, $\overline{\text{WRTEN2}}$). A maximum value of 255 can be programmed for either X or Y (see Figure 4). To use the default values of X = Y = 64, $\overline{\text{PEN}}$ must be held high.
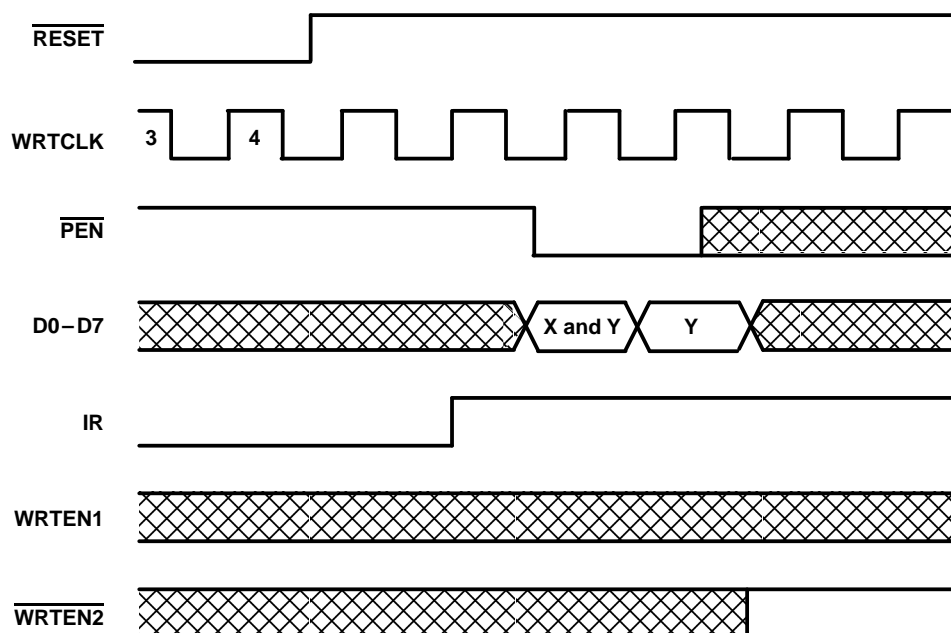

Figure 4. Programming X and Y Separately

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} .... −0.5 V to 7 V
Input voltage, V_I .... 7 V
Voltage applied to a disabled 3-state output .... 5.5 V
Operating free-air temperature range, T_A .... 0°C to 70°C
Storage temperature range, T_{stg} .... −65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions

			'ACT7803-15		'ACT7803-20		'ACT7803-25		'ACT7803-40		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		4.5	5.5	4.5	5.5	4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage		2		2		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8		0.8		0.8	V
I_{OH}	High-level output current	Q outputs, Flags		−8		−8		−8		−8	mA
I_{OL}	Low-level output current	Q outputs		16		16		16		16	mA
		Flags		8		8		8		8	
f_{clock}	Clock frequency			67		50		40		25	MHz
t_w	Pulse duration	WRTCLK high or low	6		7		8		12		ns
		RDCLK high or low	6		7		8		12		
		PEN low	8		9		9		12		
t_{su}	Setup time	D0–D17 before WRTCLK↑	4		5		5		5		ns
		WRTEN1, WRTEN2 before WRTCLK↑	4		5		5		5		
		OE1, OE2 before RDCLK↑	5		5		6		6		
		RDEN before RDCLK↑	4		5		5		5		
		Reset: RESET low before first WRTCLK↑ and RDCLK↑†	5		6		6		6		
		PEN before WRTCLK↑	5		6		6		6		
t_h	Hold time	D0–D17 after WRTCLK↑	0		0		0		0		ns
		WRTEN1, WRTEN2 after WRTCLK↑	0		0		0		0		
		OE1, OE2, RDEN after RDCLK↑	0		0		0		0		
		Reset: RESET low after fourth WRTCLK↑ and RDCLK↑†	2		2		2		2		
		PEN high after WRTCLK↓	0		0		0		0		
		PEN low after WRTCLK↑	2		2		2		2		
T_A	Operating free-air temperature		0	70	0	70	0	70	0	70	°C

† To permit the clock pulse to be utilized for reset purposes

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V_{OH}		$V_{CC} = 4.5$ V,	$I_{OH} = -8$ mA	2.4			V
V_{OL}	Flags	$V_{CC} = 4.5$ V,	$I_{OL} = 8$ mA			0.5	V
	Q outputs	$V_{CC} = 4.5$ V,	$I_{OL} = 16$ mA			0.5	
I_I		$V_{CC} = 5.5$ V,	$V_I = V_{CC}$ or 0			±5	µA
I_{OZ}		$V_{CC} = 5.5$ V,	$V_O = V_{CC}$ or 0			±5	µA
I_{CC}		$V_I = V_{CC} - 0.2$ V or 0				400	µA
ΔI_{CC}‡		$V_{CC} = 5.5$ V,	One input at 3.4 V, Other inputs at V_{CC} or GND			1	mA
C_i		$V_I = 0$,	$f = 1$ MHz			4	pF
C_o		$V_O = 0$,	$f = 1$ MHz			8	pF

† All typical values are at $V_{CC} = 5$ V, $T_A = 25°C$.
‡ This is the supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, $C_L = 50$ pF (unless otherwise noted) (see Figures 9 and 10)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	'ACT7803-15			'ACT7803-20		'ACT7803-25		'ACT7803-40		UNIT
			MIN	TYP†	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}	WRTCLK or RDCLK		67			50		40		25		MHz
t_{pd}	RDCLK↑	Any Q	4	9.5	12	4	13	4	15	4	20	ns
t_{pd}§				8.5								
t_{pd}	WRTCLK↑	IR	3		8.5	3	11	3	13	3	15	ns
t_{pd}	RDCLK↑	OR	3		8.5	3	11	3	13	3	15	ns
t_{pd}	WRTCLK↑	AF/AE	7		16.5	7	19	7	21	7	23	ns
t_{pd}	RDCLK↑	AF/AE	7		17	7	19	7	21	7	23	ns
t_{PLH}	WRTCLK↑	HF	7		15	7	17	7	19	7	21	ns
t_{PHL}	RDCLK↑		7		15.5	7	18	7	20	7	22	
t_{PLH}	$\overline{RESET}$ low	AF/AE	2		9	2	11	2	13	2	15	ns
t_{PHL}		HF	2		10	2	12	2	14	2	16	
t_{en}	$\overline{OE1}$, $\overline{OE2}$	Any Q	2		8.5	2	11	2	11	2	11	ns
t_{dis}			2		9.5	2	11	2	14	2	14	

§ This parameter is measured with a 30-pF load (see Figure 5).

operating characteristics, $V_{CC} = 5$ V, $T_A = 25°C$

PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance	Outputs enabled	$C_L = 50$ pF, $f = 5$ MHz	53	pF

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TYPICAL CHARACTERISTICS

PROPAGATION DELAY TIME
vs
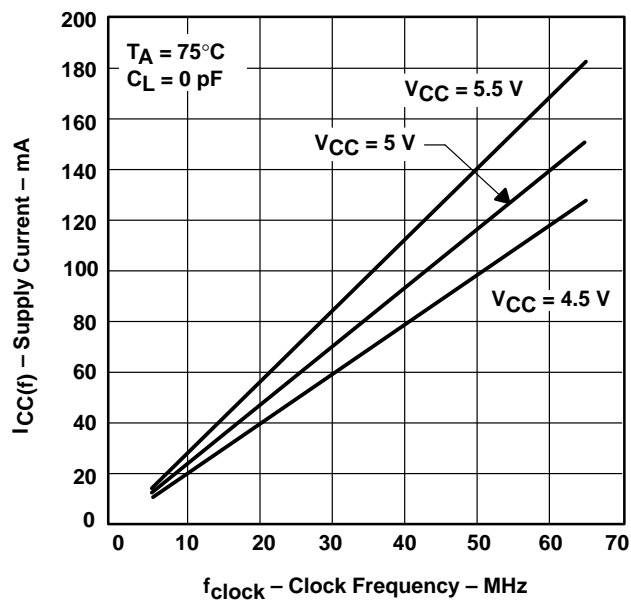**LOAD CAPACITANCE**
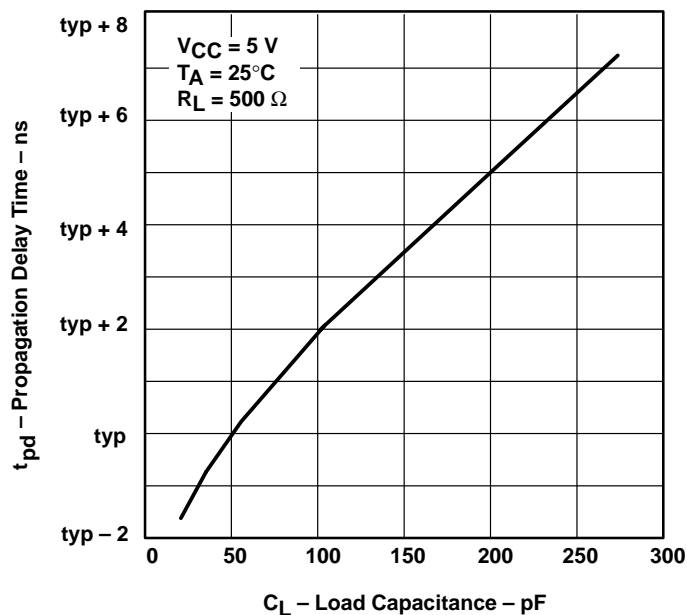
Figure 5

SUPPLY CURRENT
vs
CLOCK FREQUENCY

Figure 6

TYPICAL CHARACTERISTICS

calculating power dissipation

With $I_{CC(f)}$ taken from Figure 6, the maximum power dissipation (P_T) based on all data outputs changing states on each read can be calculated by:

$$P_T = V_{CC(f)} \times [I_{CC(f)} + (N \times \Delta I_{CC} \times dc)] + \Sigma(C_L \times V_{CC}^2 \times f_o)$$

A more accurate power calculation based on device use and average number of data outputs switching can be found by:

$$P_T = V_{CC} \times [I_{CC(I)} + (N \times \Delta I_{CC} \times dc)] + \Sigma(C_{pd} \times V_{CC}^2 \times f_i) + \Sigma(C_L \times V_{CC}^2 \times f_o)$$

where:

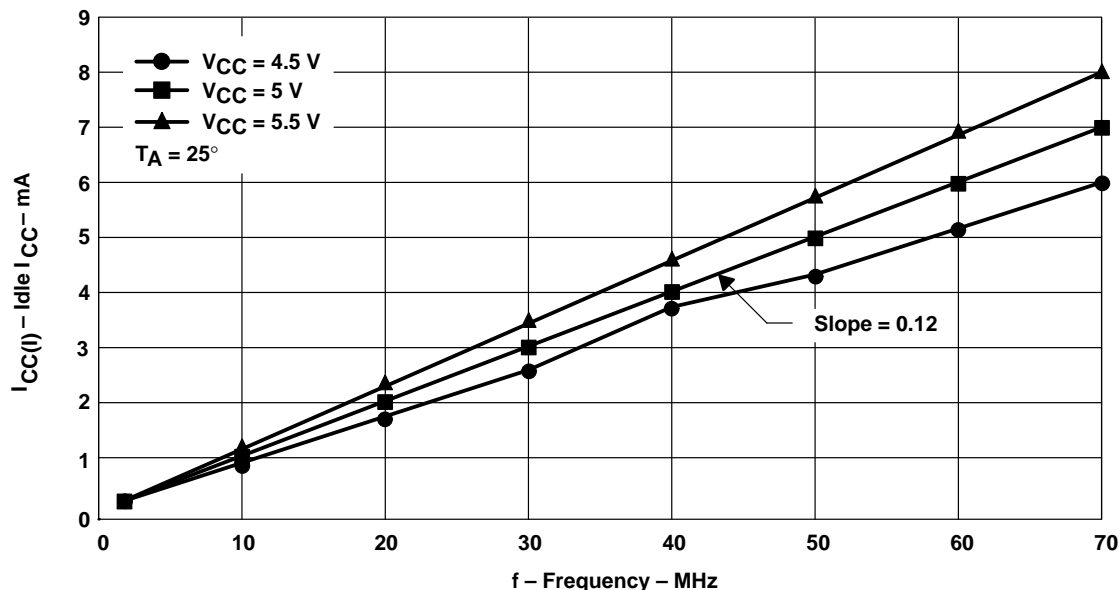|		
$I_{CC(I)}$	=	idle I_{CC} maximum (see Figure 7)
N	=	number of inputs driven by a TTL device
ΔI_{CC}	=	increase in supply current
dc	=	duty cycle of inputs at a TTL high level of 3.4 V
C_{pd}	=	power dissipation capacitance
C_L	=	output capacitive load
f_i	=	data input frequency
f_o	=	data output frequency

Figure 7. SN74ACT7803 Idle I_{CC} With RDCLK or WRTCLK Switching
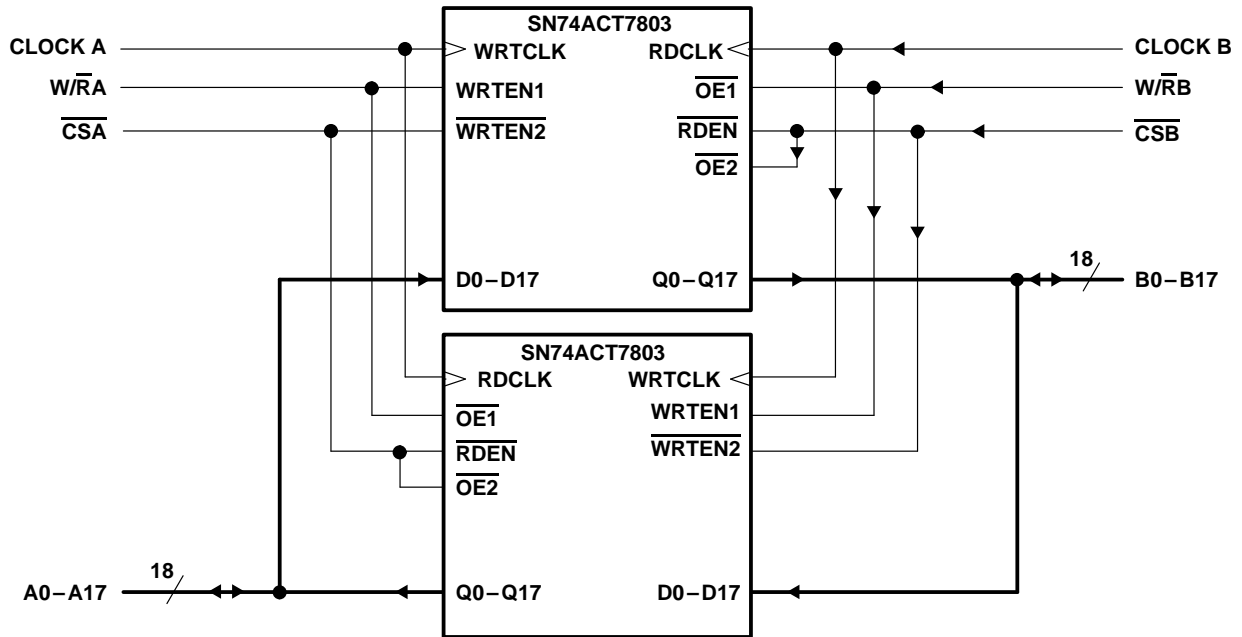
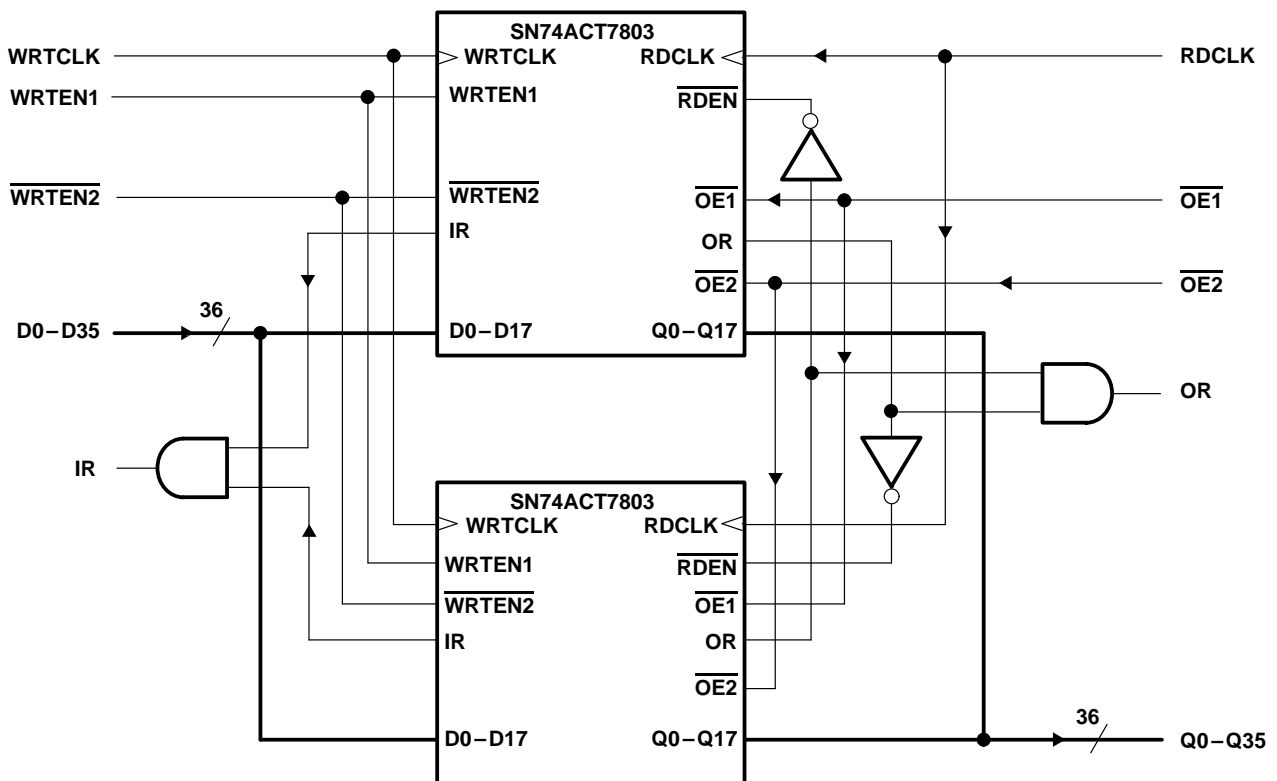## APPLICATION INFORMATION

Figure 8. Bidirectional Configuration

Figure 9. Word-Width Expansion: 512 × 36 Bits

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PARAMETER MEASUREMENT INFORMATION

LOAD CIRCUIT

From Output Under Test

R_L = 500 Ω C_L = 50 pF

TOTEM-POLE OUTPUTS

Input   3 V   1.5 V   GND

t_{pd} t_{pd}

Output   3 V   1.5 V   0 V

Figure 10. Standard CMOS Outputs (IR, OR, HF, AF/AE)

LOAD CIRCUIT

7 V

S1

R_L = R1 = R2

R1

From Output Under Test   Test Point

C_L R2

VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

Input   1.5 V   1.5 V   3 V   0 V

t_{PZL} t_{PLZ} ≈ 3.5 V

Output   1.5 V V_{OL} 0.3 V

t_{PZH} t_{PHZ} V_{OH} 0.3 V

Output   1.5 V   ≈ 0 V

PARAMETER		R1, R2	C_L†	S1
t_{en}	t_{PZH}	500 Ω	50 pF	Open
	t_{PZL}			Closed
t_{dis}	t_{PHZ}	500 Ω	50 pF	Open
	t_{PLZ}			Closed
t_{pd}		500 Ω	50 pF	Open

† Includes probe and test-fixture capacitance

Figure 11. 3-State Outputs (Any Q)

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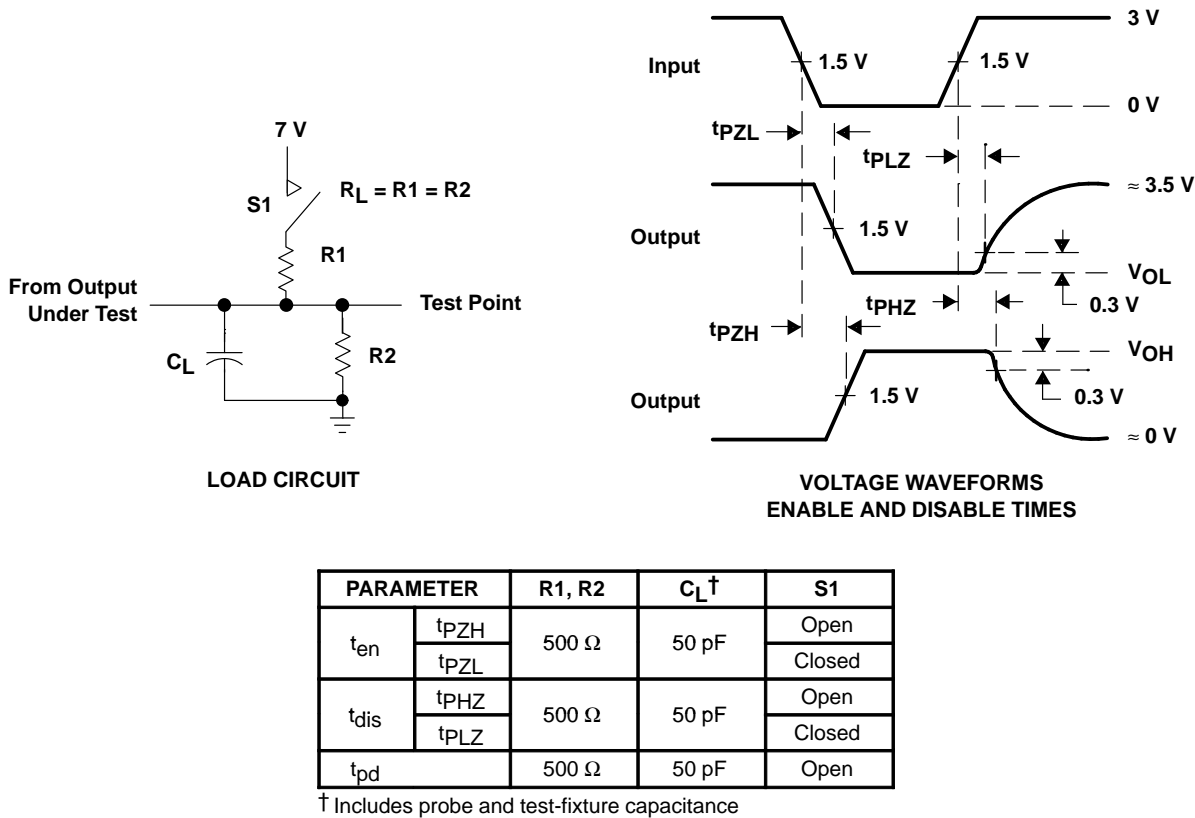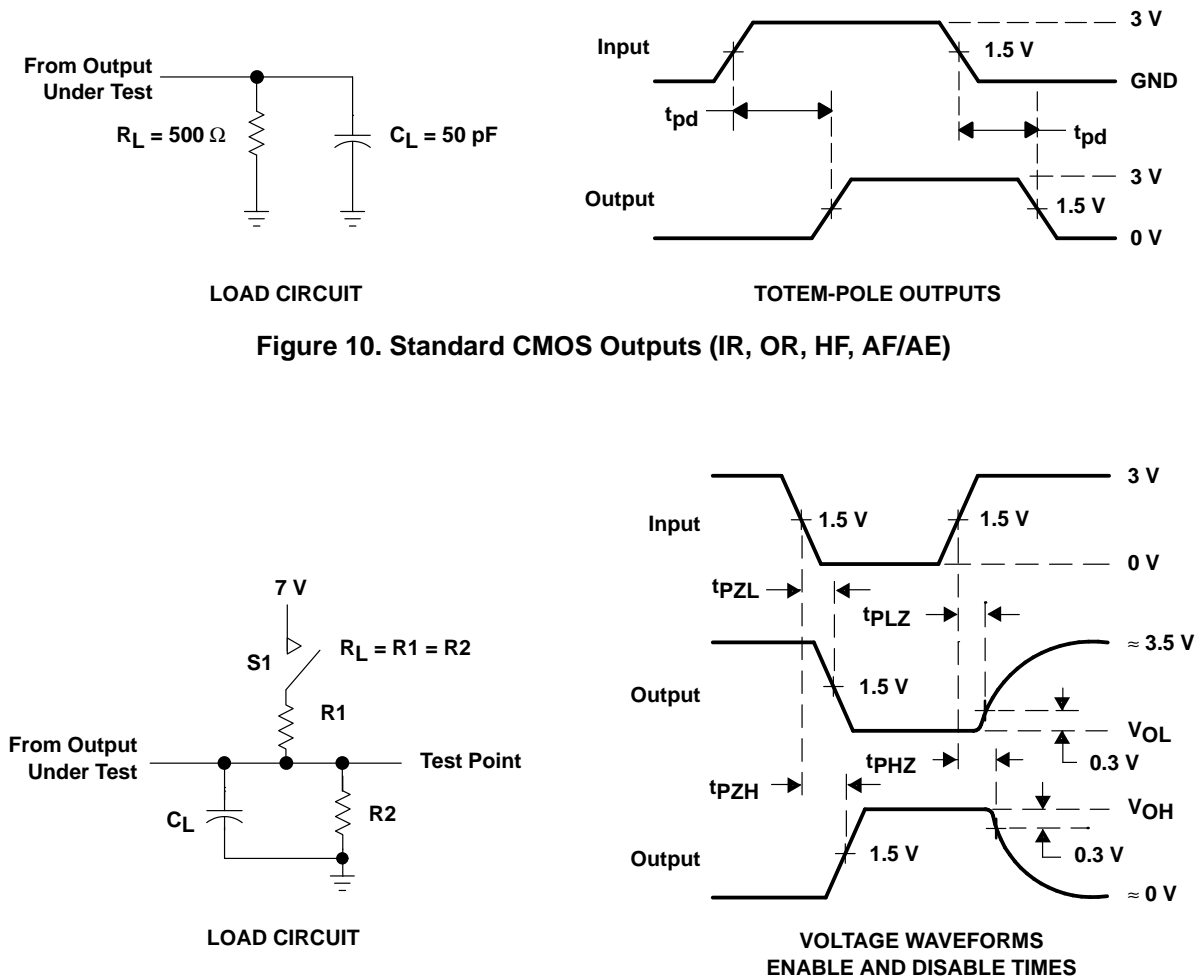
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